

**Product data sheet** 

# 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

# 2. Features and benefits

- Low threshold voltage
- Trench MOSFET technology
- Side wettable flanks for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- AEC-Q101 qualified

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

# 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Symbol	Falameter	conditions		IVIIII	тур	IVIAN	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS}$ = 4.5 V; $T_{amb}$ = 25 °C	[1]	-	-	9	А
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C		-	10	14	mΩ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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# 5. Pinning information

Table 2. Pinning information	
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Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		D
2	D	drain		
3	G	gate		G ← → 🔄 本 🔪
4	S	source		
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S
7	D	drain		017aaa255
8	S	source		

# 6. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMPB10XNEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220		

# 7. Marking

Type number	Marking code
PMPB10XNEA	4E

# 8. Limiting values

#### Table 5. Limiting values

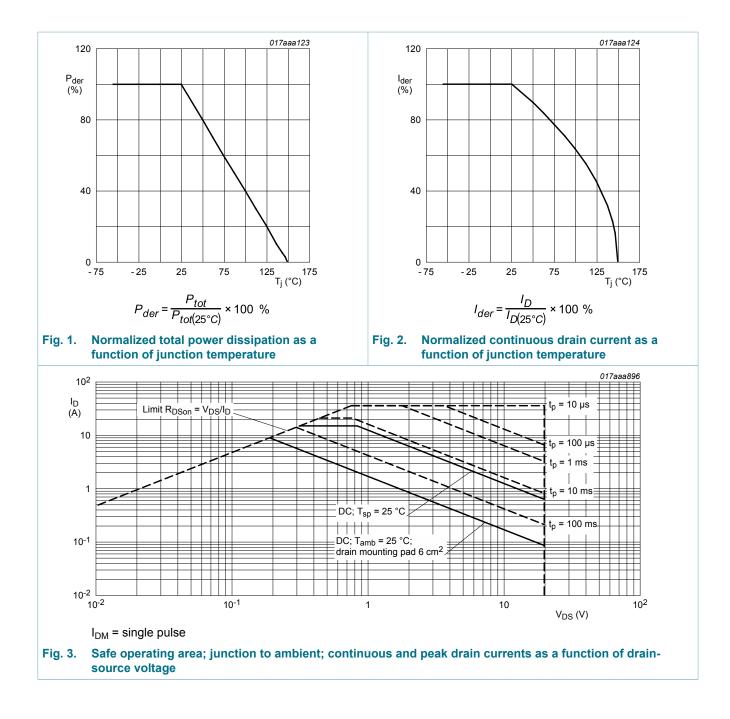
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	9	А
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	5.7	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	36	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	1.7	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain	n diode			I		
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	2	А
ESD maximu	um rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ	[2]	-	1000	V
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I <sub>D</sub> = 2 A; DUT in avalanche (unclamped)		-	21	mJ

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

[2] Measured between all pins.

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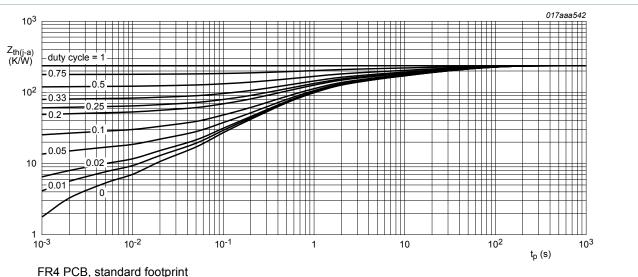
### 9. Thermal characteristics

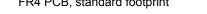
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	235	270	K/W
			[2]	-	67	74	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	5	10	K/W

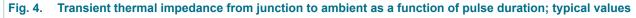
Table 6 Thormal characteristics

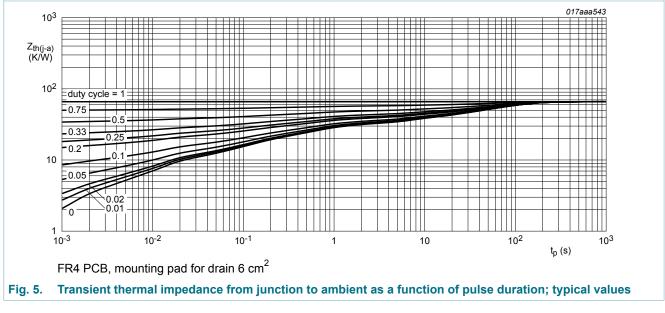
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.









PMPB10XNEA

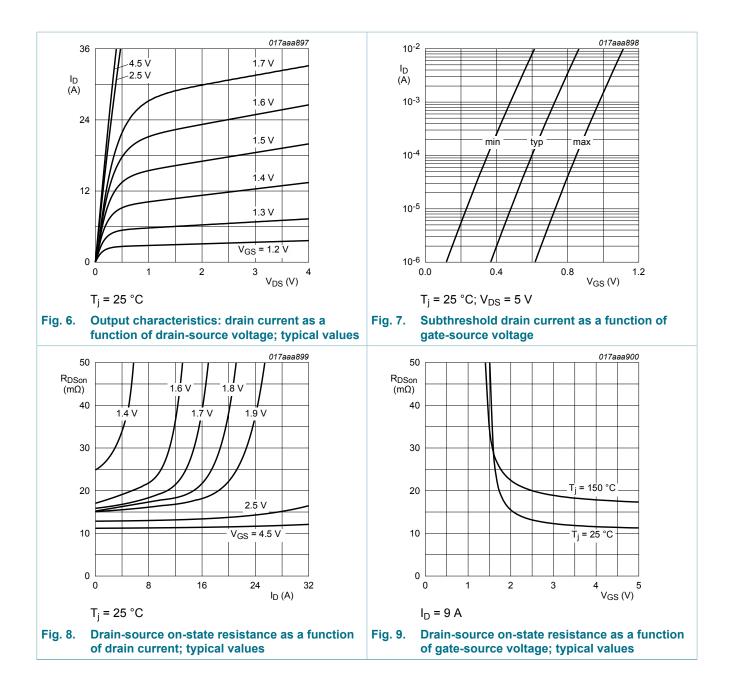
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = 250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	0.4	0.65	0.9	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
Doon	drain-source on-state	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C	-	10	14	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 150 °C	-	15	21	mΩ
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 8 A; T <sub>j</sub> = 25 °C	-	12	18	mΩ
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 3.7 A; T <sub>j</sub> = 25 °C	-	16	25	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 9 A; T <sub>j</sub> = 25 °C	-	60	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	2	-	Ω
Dynamic ch	aracteristics	· · ·			1	
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; $I_{D}$ = 6 A; $V_{GS}$ = 4.5 V;	-	23	34	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	2.6	-	nC
Q <sub>GD</sub>	gate-drain charge		-	4.5	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	2175	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	235	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	205	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; I <sub>D</sub> = 6 A; V <sub>GS</sub> = 4.5 V;	-	13	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	35	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	54	-	ns
t <sub>f</sub>	fall time		-	50	-	ns
Source-drai	n diode	· · · · · ·	·			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 2 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.6	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 2 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	13	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 10 V; T <sub>j</sub> = 25 °C	-	5	-	nC

#### Nexperia

# **PMPB10XNEA**

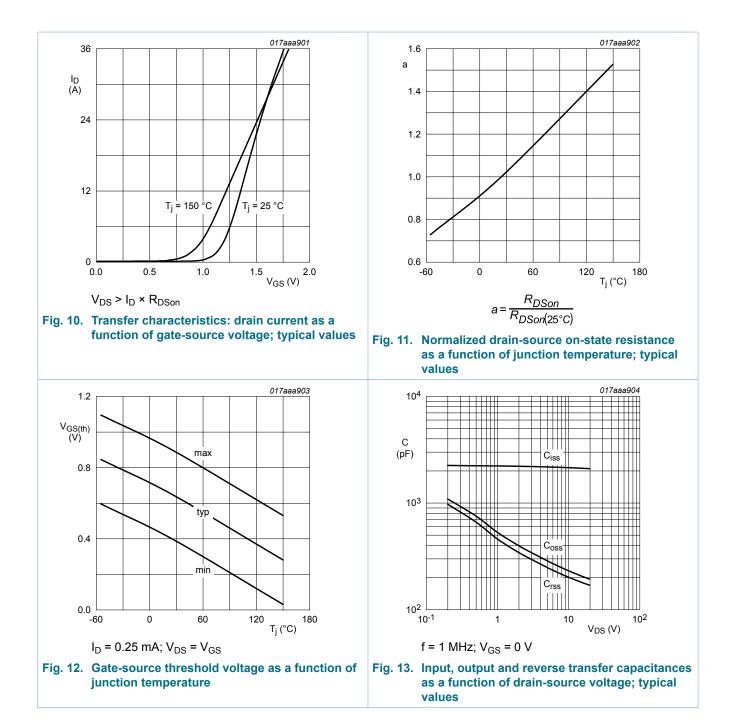
#### 20 V, N-channel Trench MOSFET



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# **PMPB10XNEA**

#### 20 V, N-channel Trench MOSFET

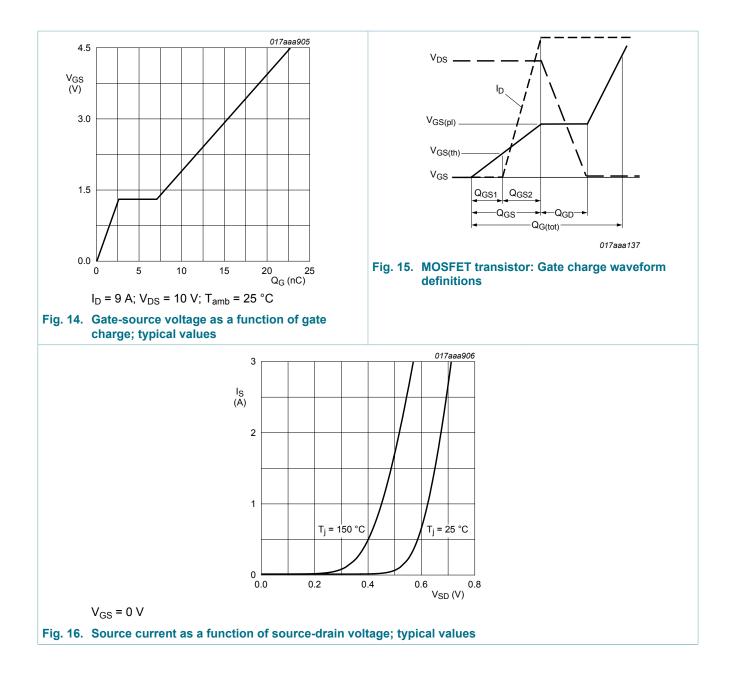


PMPB10XNEA

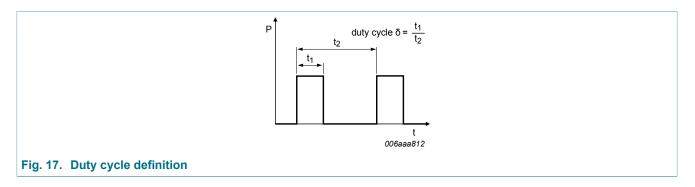
### Nexperia

# **PMPB10XNEA**

#### 20 V, N-channel Trench MOSFET



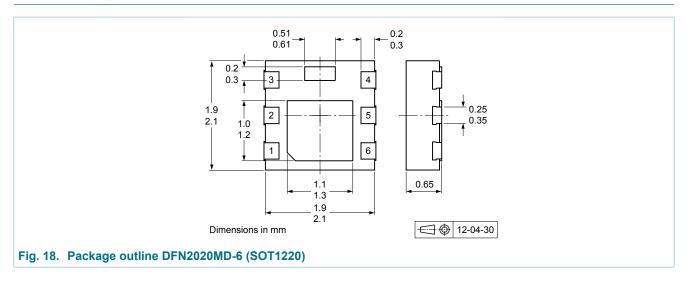
### 11. Test information



#### **Quality information**

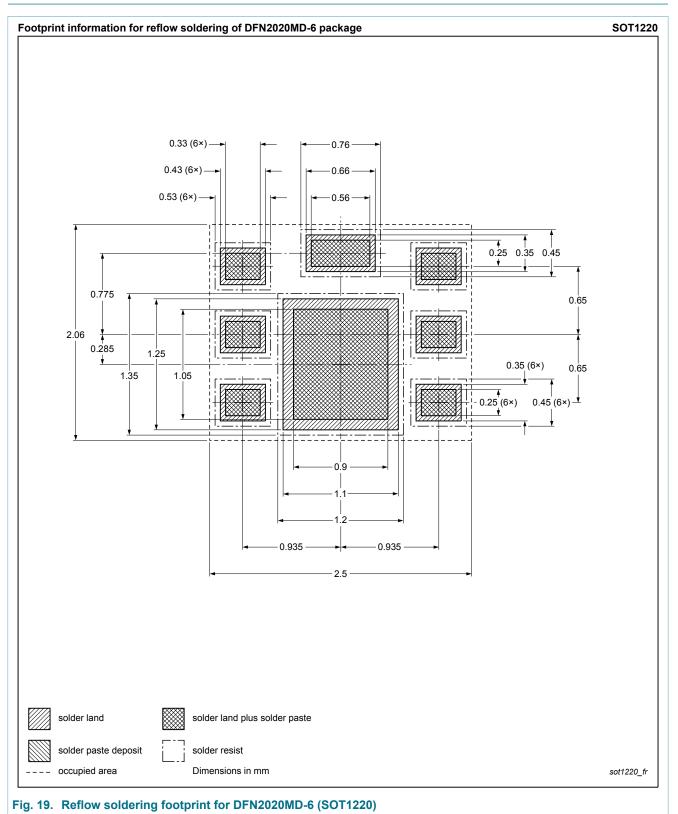
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



#### 20 V, N-channel Trench MOSFET

# 13. Soldering



PMPB10XNEA

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# 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMPB10XNEA v.1	20180327	Product data sheet	-	-		

#### 20 V, N-channel Trench MOSFET

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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